

85V 4.0mΩ N-Ch Power MOSFET

Features

- Ultra Low $R_{DS(ON)}$
- Low Gate Charge
- High Current Capability
- 100% UIS Tested, 100% Rg Tested

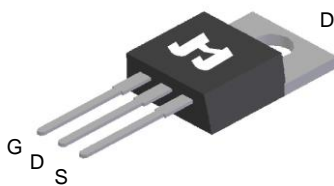
Applications

- Power Management in Telecom., Industrial Automation, CE
- Current Switching in DC/DC & AC/DC Sub-systems
- Motor Driving in Power Tool, E-bike

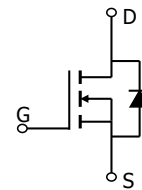
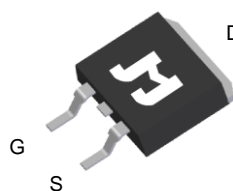
Product Summary

Parameter	Typ.	Unit
V_{DS}	85	V
$V_{GS(th)}$	2.8	V
I_D (@ $V_{GS} = 10V$)	132	A
$R_{DS(ON)}$ (@ $V_{GS} = 10V$)	4.0	mΩ

TO220-3L Top View



TO263-3L Top View

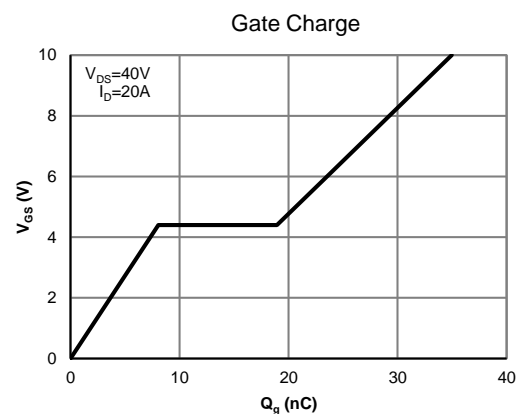
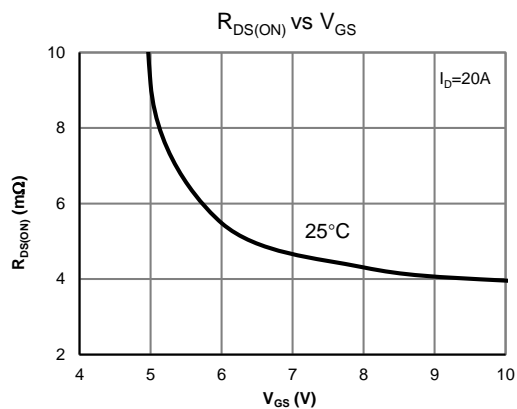


Ordering Information

Device	Package	# of Pins	Marking	MSL	T_J (°C)	Media	Quantity (pcs)
JMSH0804BCS-U	TO220-3L	3	SH0804BS	N/A	-55~150	Tube	50
JMSH0804BES-13	TO263-3L	3	SH0804BS	3	-55~150	13-inch Reel	800

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	85	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	$T_C=25^\circ\text{C}$	132
		$T_C=70^\circ\text{C}$	105
Pulsed Drain Current	I_{DM}	500	A
Avalanche Current	I_{AS}	60	A
Avalanche Energy (@ $L=0.1\text{mH}$)	E_{AS}	180	mJ
Power Dissipation	P_D	$T_C=25^\circ\text{C}$	156
		$T_C=70^\circ\text{C}$	100
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C





Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	85			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 68\text{V}$, $V_{GS} = 0\text{V}$ $T_J = 55^\circ\text{C}$			1 5	μA
Gate-Body leakage current	I_{GSS}	$V_{DS} = 0\text{V}$, $V_{GS} = \pm 20\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	2.0	2.8	4.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{V}$, $I_D = 20\text{A}$		4.0	5.0	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{V}$, $I_D = 20\text{A}$		64		S
Diode Forward Voltage	V_{SD}	$I_S = 1\text{A}$, $V_{GS} = 0\text{V}$		0.7	1.0	V
Diode Continuous Current	I_S	$T_C = 25^\circ\text{C}$			156	A

DYNAMIC PARAMETERS

Input Capacitance	C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 40\text{V}$, $f = 1\text{MHz}$		2083		pF
Output Capacitance	C_{oss}			1142		pF
Reverse Transfer Capacitance	C_{rss}			18		pF
Gate resistance	R_g	$V_{GS} = 0\text{V}$, $V_{DS} = 0\text{V}$, $f = 1\text{MHz}$		2.0		Ω

SWITCHING PARAMETERS

Total Gate Charge (@ $V_{GS} = 10\text{V}$)	Q_g	$V_{DS} = 40\text{V}$, $I_D = 20\text{A}$		35		nC
Total Gate Charge (@ $V_{GS} = 6\text{V}$)	Q_g			23.5		nC
Gate Source Charge	Q_{gs}			8		nC
Gate Drain Charge	Q_{gd}			11		nC
Turn-On DelayTime	$t_{D(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 40\text{V}$, $R_L = 2\Omega$, $R_{GEN} = 6\Omega$		14		ns
Turn-On Rise Time	t_r			39		ns
Turn-Off DelayTime	$t_{D(off)}$			34		ns
Turn-Off Fall Time	t_f			25		ns
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 20\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$		60		ns
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F = 20\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$		122		nC

Thermal Performance

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	45	55	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.65	0.8	$^\circ\text{C}/\text{W}$

Typical Electrical & Thermal Characteristics

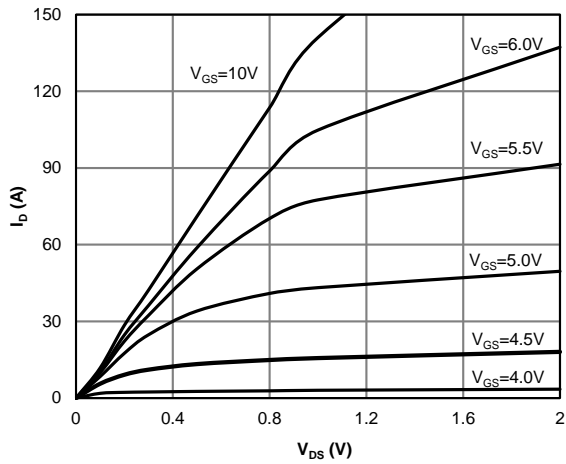


Figure 1: Saturation Characteristics

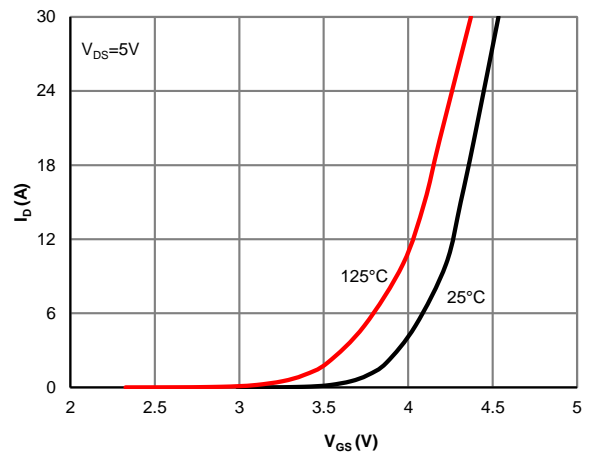


Figure 2: Transfer Characteristics

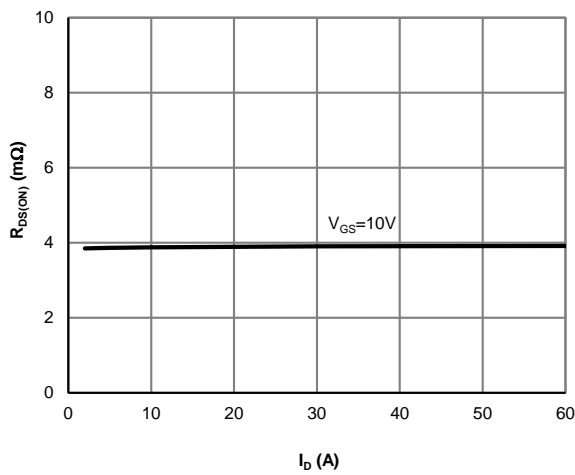


Figure 3: $R_{DS(ON)}$ vs. Drain Current

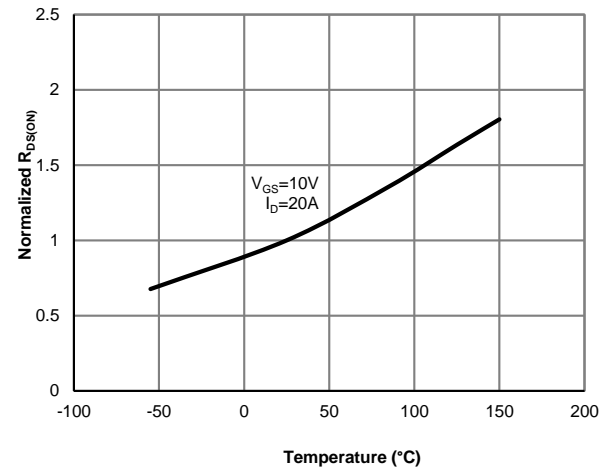


Figure 4: Normalized $R_{DS(ON)}$ vs. Junction Temperature

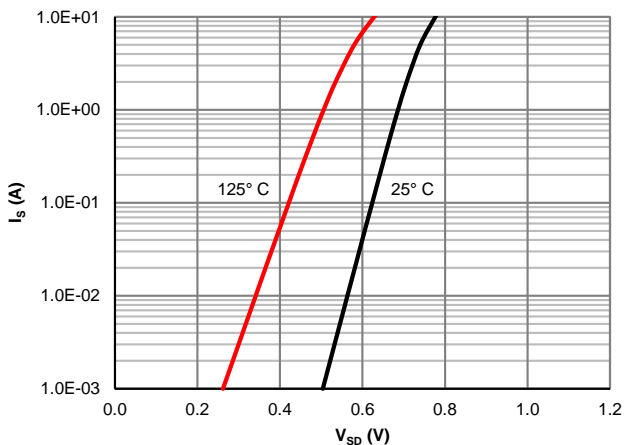


Figure 5: Body-Diode Characteristics

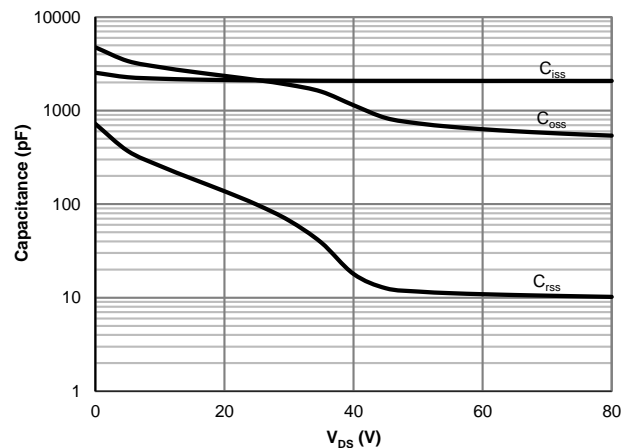


Figure 6: Capacitance Characteristics

Typical Electrical & Thermal Characteristics

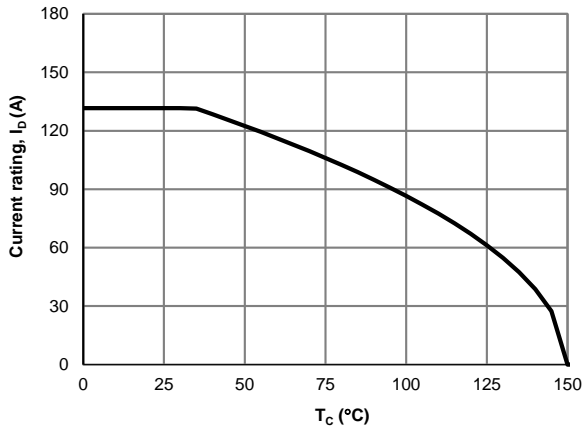


Figure 7: Current De-rating

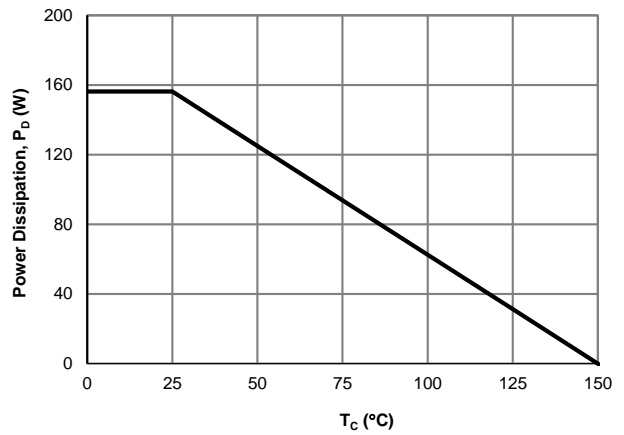


Figure 8: Power De-rating

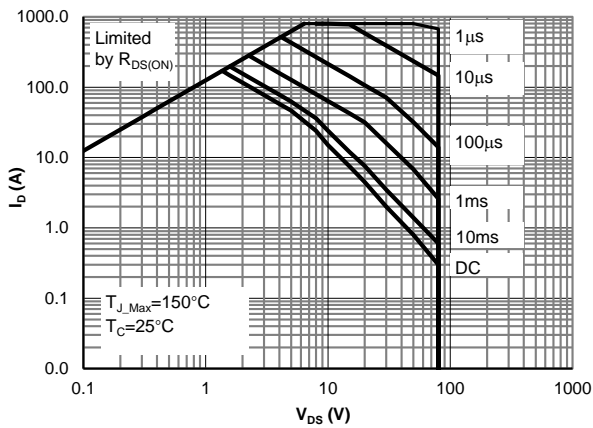


Figure 9: Maximum Safe Operating Area

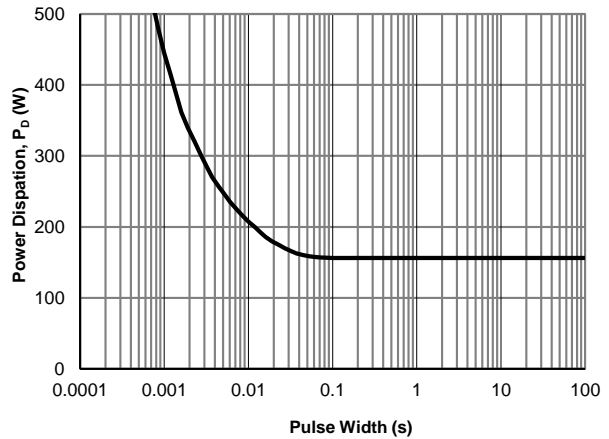


Figure 10: Single Pulse Power Rating, Junction-to-Case

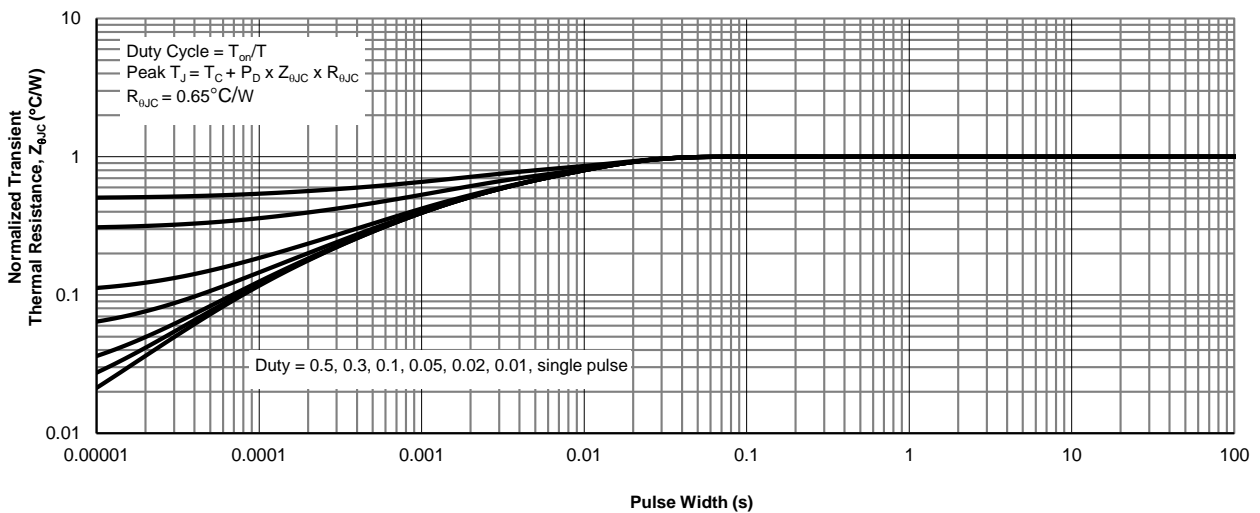
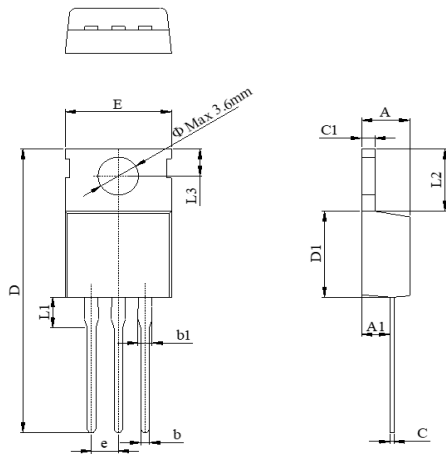


Figure 11: Normalized Maximum Transient Thermal Impedance

TO220-3L Package Information (all units in mm)

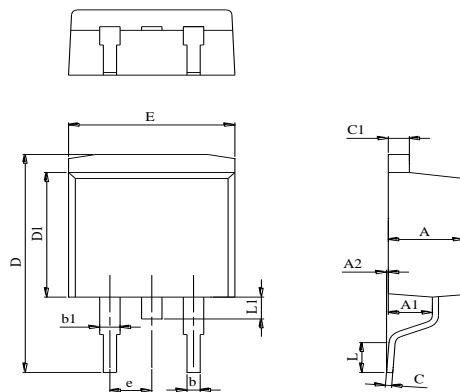
Package Outline



DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	4.37		4.70
A1	2.20		3.00
b	0.70		0.95
b1	1.14		1.70
C	0.45		0.60
C1	1.23		1.40
D	28.00		29.80
D1	8.80		9.90
E	9.70		10.50
L1			3.80
L2	6.25		6.90
L3	2.40		3.00
e		2.54 BSC	

TO263-3L Package Information (all units in mm)

Package Outline



DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	4.37		4.77
A1	2.30		2.89
A2	0.00	0.10	0.25
b	0.70		0.96
b1	1.17		1.47
C	0.30		0.55
C1	1.22		1.42
D	14.10		15.80
D1	8.50		9.60
E	9.86		10.36
L	2.00		2.60
L1			1.75
e		2.54	

Recommend Soldering Footprint

